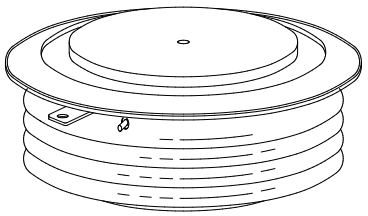
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T8C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK1200/18	1800	1800	2000
KK1200/20	2000	2000	2100

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

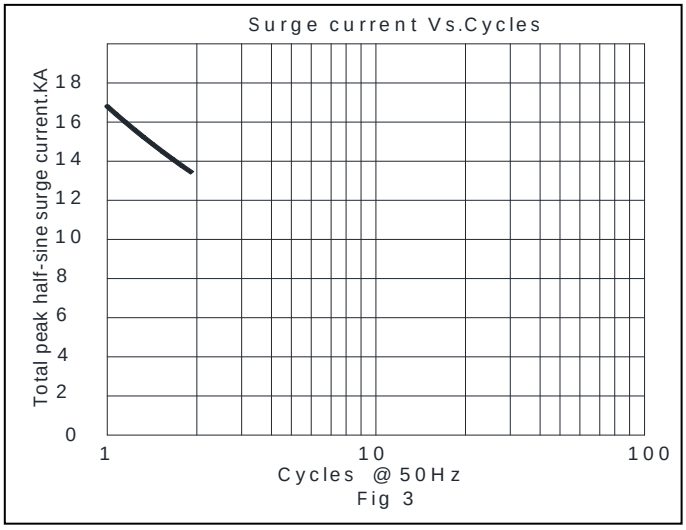
Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 80 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Notes
All ratings are specified for Tj=25 °C unless otherwise stated.
(1) All voltage ratings are specified for an applied 50Hz/60zHz sinusoidal waveform over the temperature range 0 to +125 °C
(2) 10 msec. Max. Pulse width
(3) Maximum value for Tj=125 °C.
(4) Minimum value for linear and exponential waveshape to 67% rated $V_{DRM.}$ Gate open, Tj=125 °C
(5) The value of di/dt is established in accordance with JB/T4193-2013.

C

Average value of on-state current	$I_{T(AV)}$	1200	A	Sinewave,180° conduction,Tc=55°C
RMS value of on-state current	I_{TRMS}	1884	A	Nominal value
Peak one cycle surge (non repetitive) current	I_{TSM}	16800	A	10 msec (50Hz), sinusoidal wave-shape, 180°

Peak gate power dissipation	P_{GM}	20	W
Average gate power dissipation	$P_{G(AV)}$	4	W


Surge current Vs.Cycles
Total peak half-sine surge current.KA
18
16
14
12
10
8
6
4
2
0
1
10
100
Cycles @ 50Hz
Fig 3

